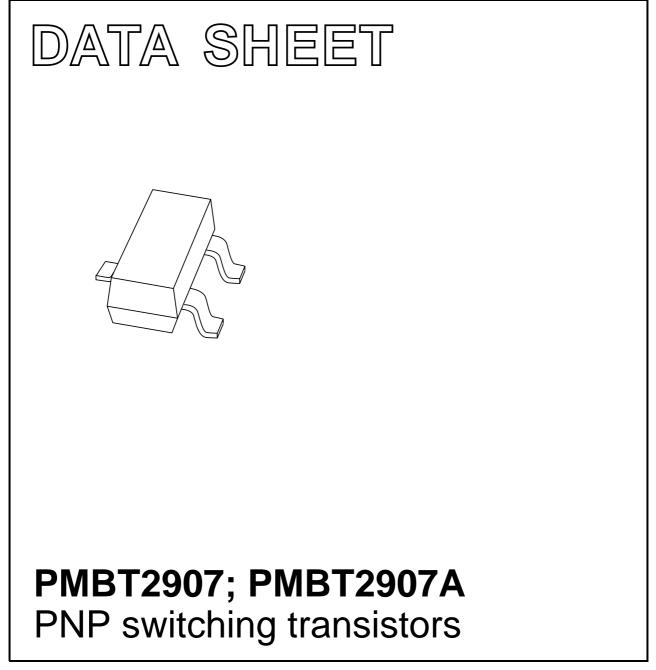
# DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 27 2004 Jan 16



### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

### APPLICATIONS

• Switching and linear amplification.

#### DESCRIPTION

PNP switching transistor in a SOT23 plastic package. NPN complements: PMBT2222 and PMBT2222A.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBT2907	*2B
PMBT2907A	*2F

#### Note

- 1. \* = p : Made in Hong Kong.
  - \* = t : Made in Malaysia.
  - \* = W: Made in China.

### **ORDERING INFORMATION**

### PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	

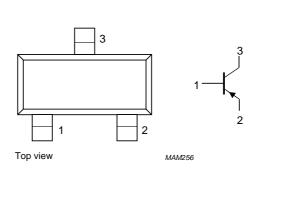


Fig.1 Simplified outline (SOT23) and symbol.

TYPE	PACKAGE		
NUMBER NAME DESCRIPTION		DESCRIPTION	VERSION
PMBT2907	_	plastic surface mounted package; 3 leads	SOT23
PMBT2907A	_	plastic surface mounted package; 3 leads	SOT23

**PMBT2907;** 

**PMBT2907A** 

# PMBT2907; PMBT2907A

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	PMBT2907		_	-40	V
	PMBT2907A		_	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
I <sub>C</sub>	collector current (DC)		-	-600	mA
I <sub>CM</sub>	peak collector current		—	-800	mA
I <sub>BM</sub>	peak base current		—	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

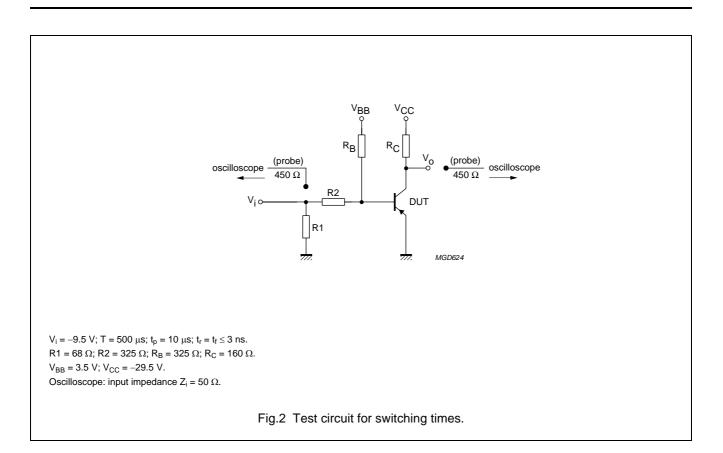
# PMBT2907; PMBT2907A

### CHARACTERISTICS

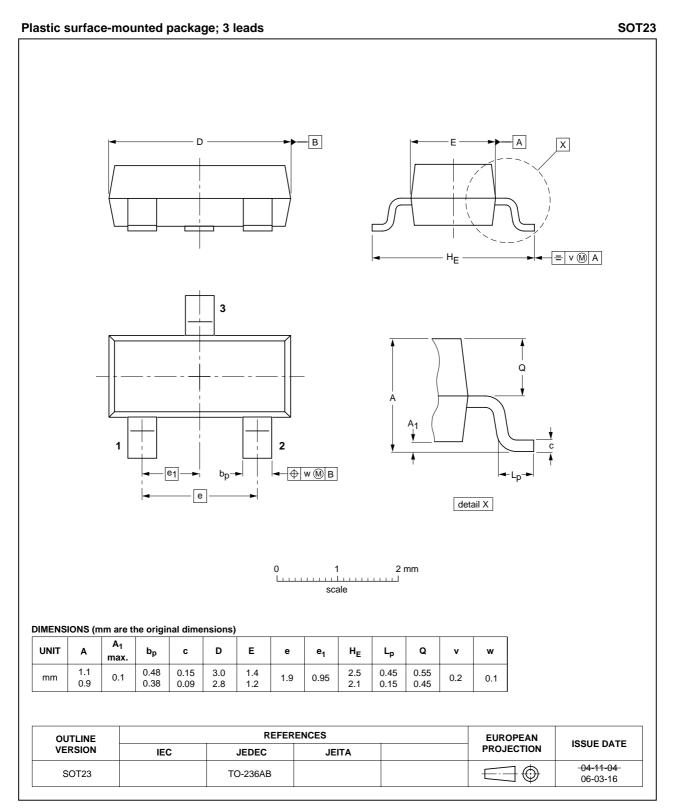
 $T_j$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -50 V			
	PMBT2907		_	-20	nA
	PMBT2907A		_	-10	nA
	collector-base cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -50 V; T <sub>j</sub> = 125 °C			
	PMBT2907		_	-20	μA
	PMBT2907A		-	-10	μA
I <sub>EBO</sub>	emitter-base cut-off current	$I_{C} = 0; V_{EB} = -5 V$	-	-50	nA
h <sub>FE</sub>	DC current gain	$I_{C} = -0.1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		35	-	
	PMBT2907A		75	-	
	DC current gain	$I_{C} = -1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		50	-	
	PMBT2907A		100	-	
	DC current gain	$I_{C} = -10 \text{ mA}; V_{CE} = -10 \text{ V}$			
	PMBT2907		75	-	
	PMBT2907A		100	_	
	DC current gain	$I_{C} = -150 \text{ mA}; V_{CE} = -10 \text{ V}$	100	300	
	DC current gain	$I_{\rm C} = -500 \text{ mA}; V_{\rm CE} = -10 \text{ V}$			
	PMBT2907		30	-	
	PMBT2907A		50	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -150 mA; I <sub>B</sub> = -15 mA	_	-400	mV
		$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}$	_	-1.6	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{\rm C} = -150 \text{ mA}; I_{\rm B} = -15 \text{ mA}$	_	-1.3	V
		$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}$	_	-2.6	V
Cc	collector capacitance	$I_E = I_e = 0; V_{CB} = -10 V; f = 1 MHz$	_	8	pF
Ce	emitter capacitance	$I_{C} = I_{c} = 0; V_{EB} = -2 V; f = 1 MHz$	_	30	pF
f <sub>T</sub>	transition frequency	$I_{C} = -50 \text{ mA}; V_{CE} = -20 \text{ V}; \text{ f} = 100 \text{ MHz}$	200	_	MHz
Switching t	imes (between 10% and 90% leve	els); (see Fig.2)		•	
t <sub>on</sub>	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$	-	40	ns
t <sub>d</sub>	delay time	I <sub>Boff</sub> = 15 mA	_	12	ns
t <sub>r</sub>	rise time		_	30	ns
t <sub>off</sub>	turn-off time		_	365	ns
ts	storage time		_	300	ns
t <sub>f</sub>	fall time		_	65	ns

# PMBT2907; PMBT2907A



### PACKAGE OUTLINE



# PMBT2907; PMBT2907A

PMBT2907; PMBT2907A

### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

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## **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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